March 2010



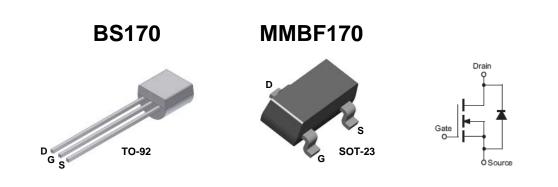
BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

General Description

These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units	
V _{DSS}	Drain-Source Voltage	60		V	
V _{DGR}	Drain-Gate Voltage ($R_{GS} \le 1M\Omega$)	60		V	
V _{GSS}	Gate-Source Voltage	±	20	V	
I _D	Drain Current - Continuous	500	500	mA	
	- Pulsed	1200	800		
T _J , T _{STG}	Operating and Storage Temperature Range	- 55 1	to 150	°C	
ΤL	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300		°C	

Thermal Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
P _D	Maximum Power Dissipation Derate above 25°C	830 6.6	300 2.4	mW mW/°C
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	150	417	°C/W

© 2010 Fairchild Semiconductor Corporation BS170 / MMBF170 Rev. E2

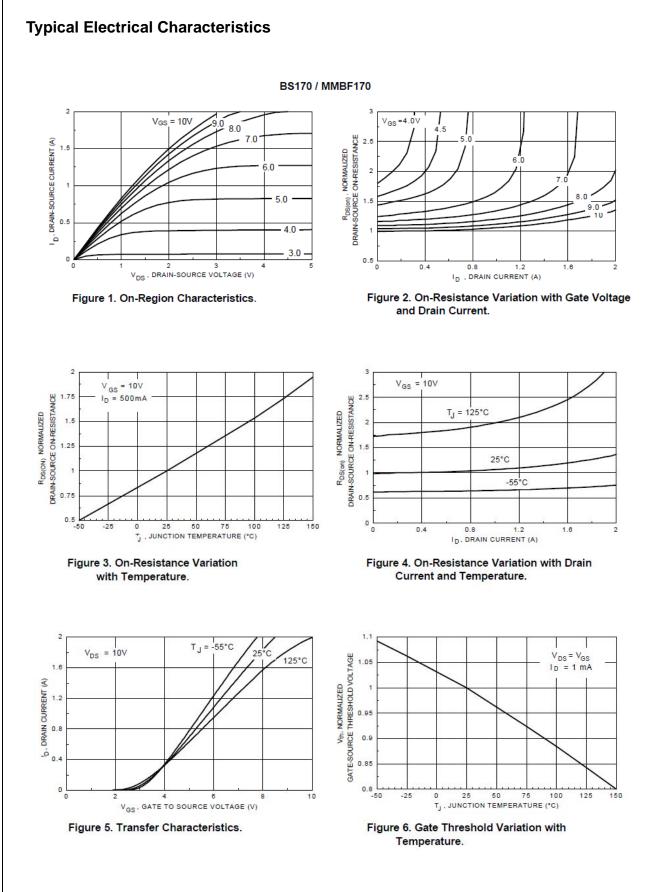
Symbol	Parameter	Conditions	Туре	Min.	Тур.	Max.	Units
OFF CHA	RACTERISTICS				1		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 100 \mu A$	All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	All			0.5	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 15V, V _{DS} = 0V	All			10	nA
ON CHAF	RACTERISTICS (Notes 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1mA$	All	0.8	2.1	3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 200mA	All		1.2	5	Ω
g _{FS} Forward Tra	Forward Transconductance	V _{DS} = 10V, I _D = 200mA	BS170		320		mS
			MMBF170		320		
Dynamic	Characteristics	L					
C _{iss}	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	All		24	40	pF
C _{oss}	Output Capacitance	f = 1.0MHz	All		17	30	pF
C _{rss}	Reverse Transfer Capacitance		All		7	10	pF
Switching	g Characteristics (Notes 1)						
t _{on}	Turn-On Time	$V_{DD} = 25V, I_D = 200mA, \\ V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, \\ V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	
t _{off}	Turn-Off Time	V_{DD} = 25V, I_D = 200mA, V_{GS} = 10V, R_{GEN} = 25 Ω	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	

Note:

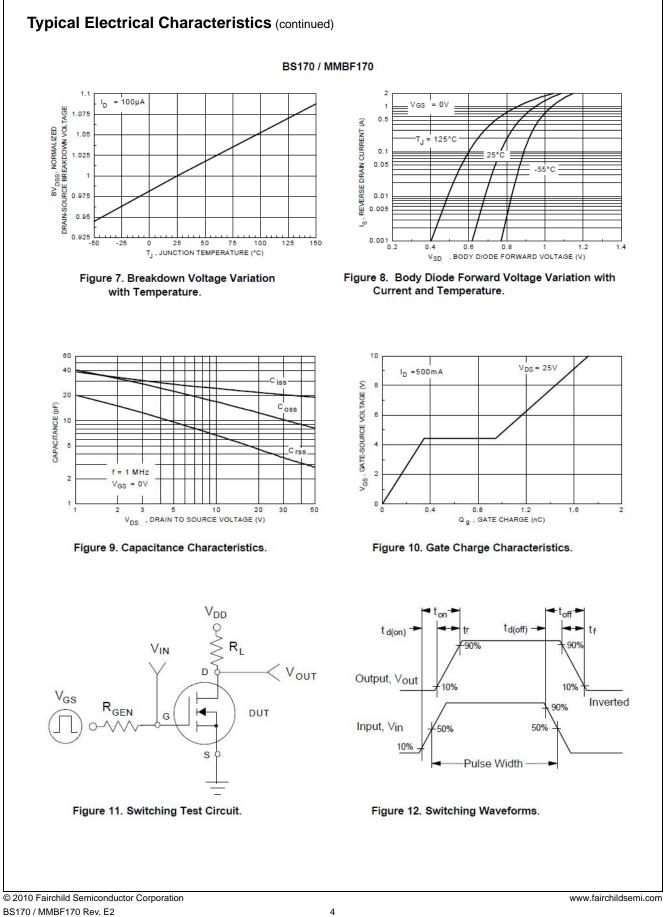
1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

Ordering Information

Part Number	Package	Package Type	Lead Frame	Pin array
BS170	TO-92	BULK	STRAIGHT	DGS
BS170_D26Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D27Z	TO-92	Tape and Reel	FORMING	DGS
BS170_D74Z	TO-92	AMMO	FORMING	DGS
BS170_D75Z	TO-92	AMMO	FORMING	DGS
MMBF170	SOT-23	Tape and Reel		

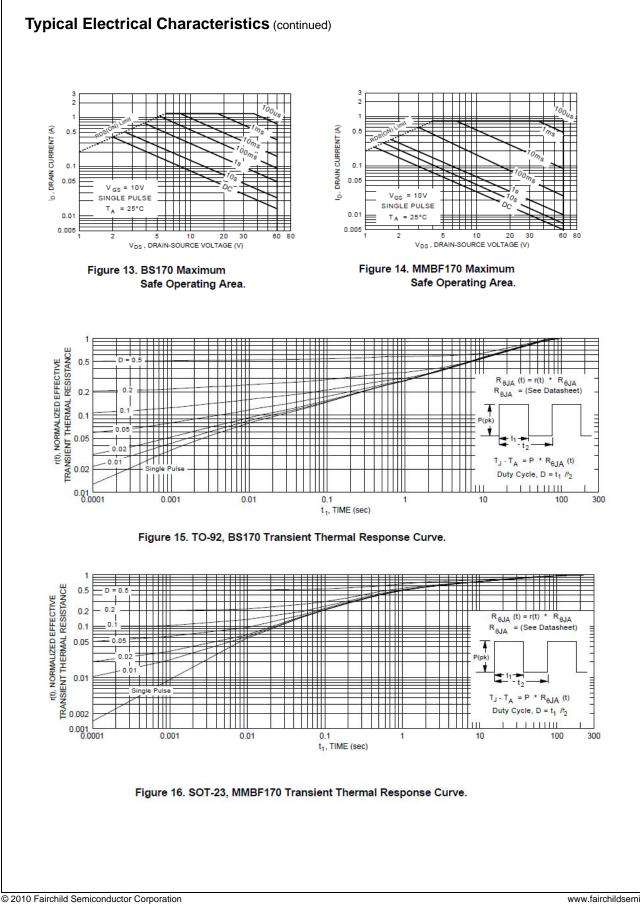


© 2010 Fairchild Semiconductor Corporation BS170 / MMBF170 Rev. E2 www.fairchildsemi.com



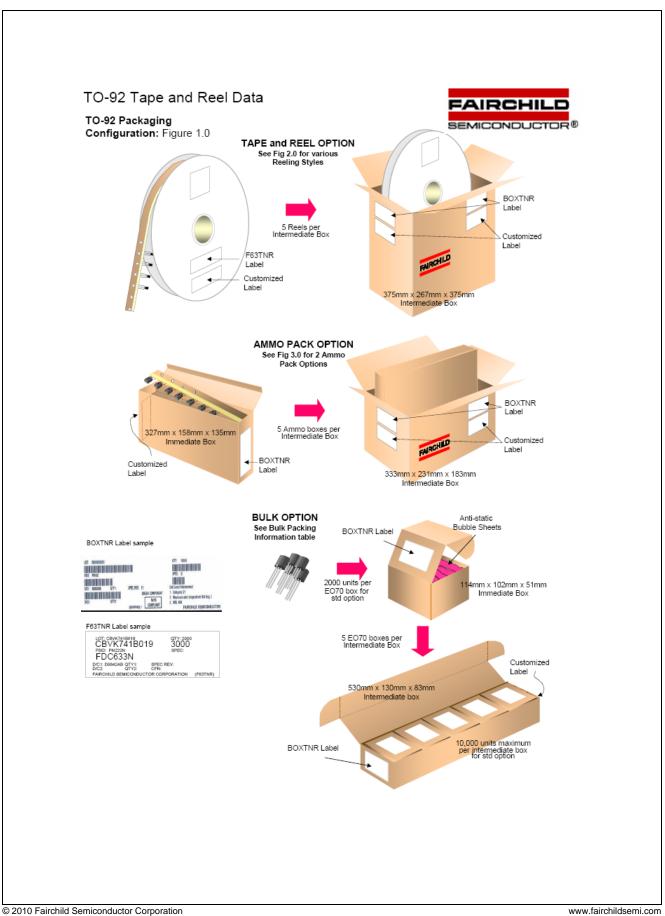
BS170 / MMBF170 — N-Channel Enhancement Mode Field Effect Transistor

4



BS170 / MMBF170 Rev. E2

BS170 / MMBF170 — N-Channel Enhancement Mode Field Effect Transistor



BS170 / MMBF170 Rev. E2

www.fairchildsemi.com

BS170 / MMBF170 — N-Channel Enhancement Mode Field Effect Transistor

TO-92 Tape and Reel Data, continued



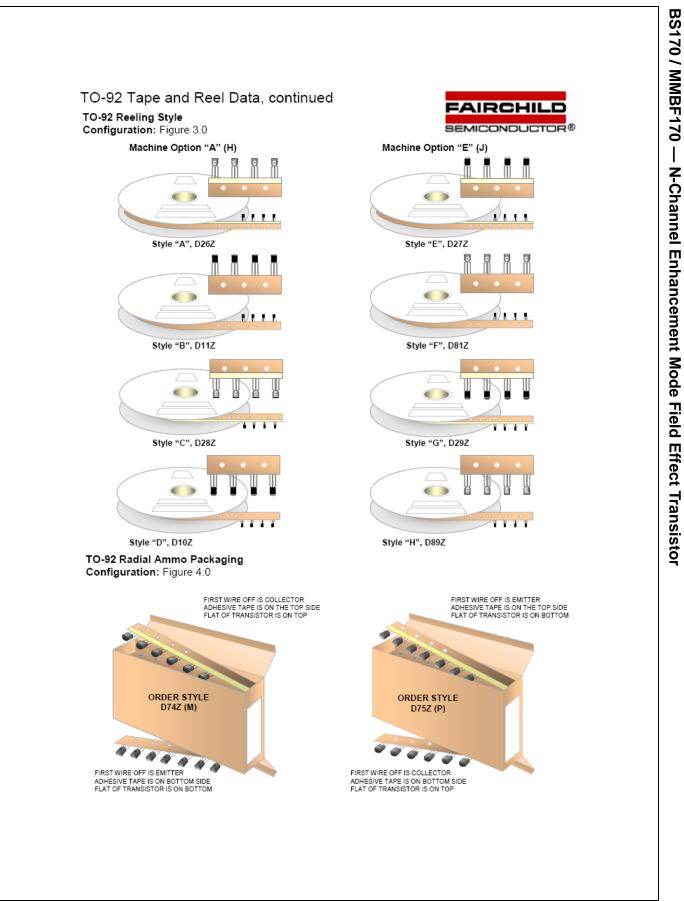
TO-92 Packing Information: Figure 2.0

TO-92 TNR/AM	IMO PACKIN	G INFORMATI	ON TABLE

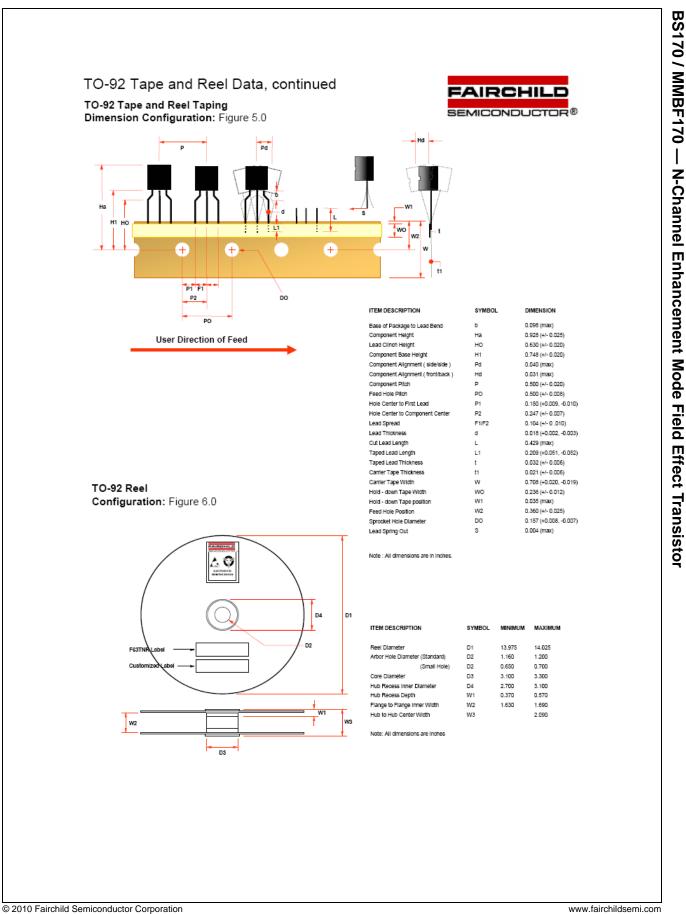
Packing	Style	Quantity	EOL code
Reel	Α	2,000	D26Z
	В	2,000	D11Z
	С	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
	н	2,000	D89Z
Ammo	M	2,000	D74Z
	Р	2,000	D75Z
	ith components	= 0.22 gm = 1.04 kg = 1.02 kg ox = 10,000 units	

TO-92 BULK PACKING INFORMATION TABLE

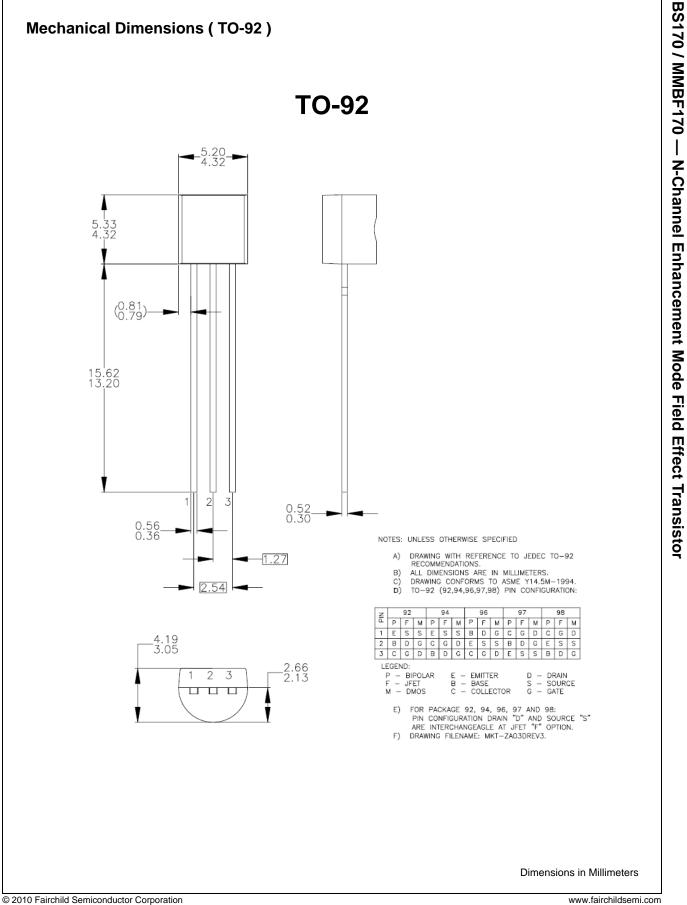
EOL CODE / FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OULTINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	×.
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0K / BOX	
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	



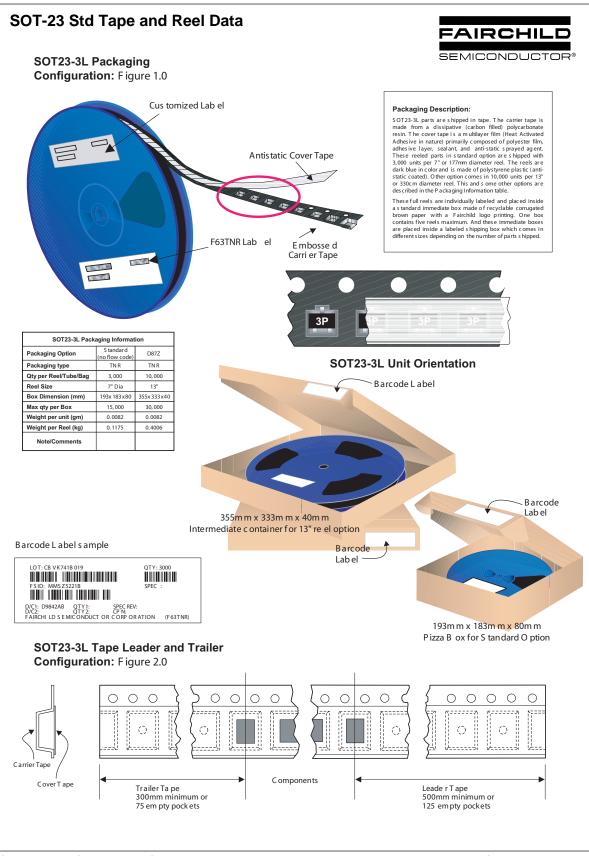
© 2010 Fairchild Semiconductor Corporation BS170 / MMBF170 Rev. E2



BS170 / MMBF170 Rev. E2

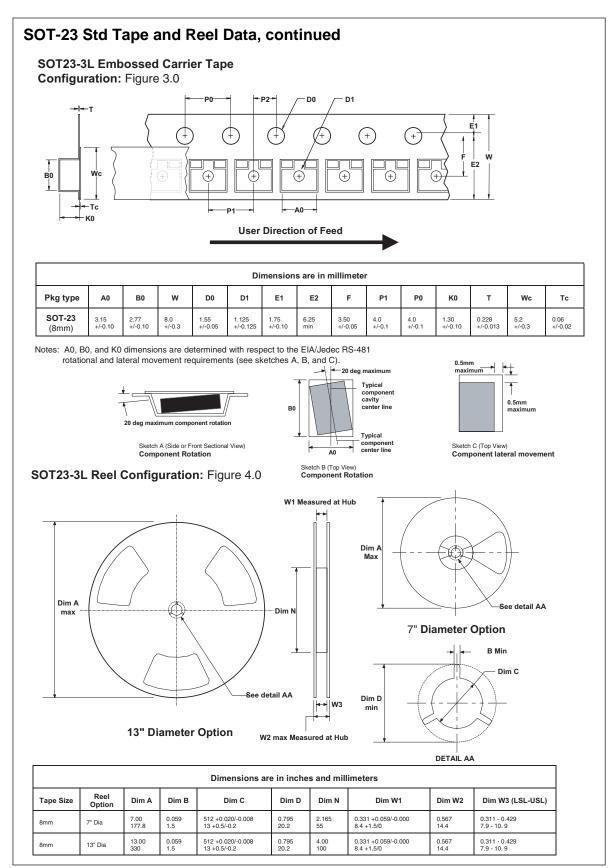


BS170 / MMBF170 Rev. E2

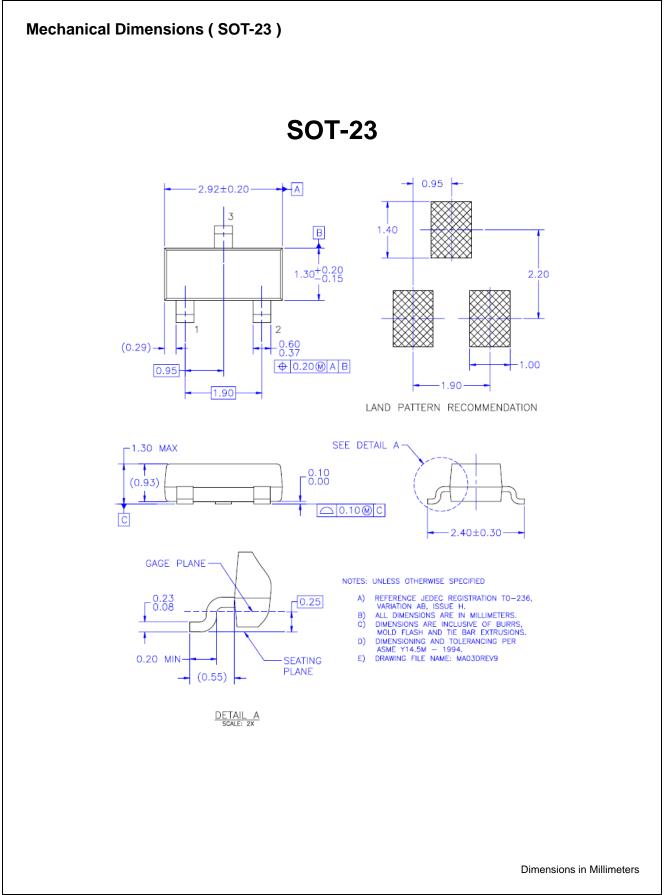


©2001 Fairchild Semiconductor Corporation

October 2004, Rev. D1



October 2004, Rev. D1



www.fairchildsemi.com

BS170 / MMBF170 — N-Channel Enhancement Mode Field Effect Transistor

© 2010 Fairchild Semiconductor Corporation BS170 / MMBF170 Rev. E2

FAIRCHILD

SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks. AccuPower™ FRFET[®] PowerTrench[®] The Power Franchise[®]

AccuPower™ Auto-SPM™ Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT™ CTL™ Current Transfer Logic™ DEUXPEED[®] Dual Cool™ EcoSPARK[®] EfficientMax™ ® Fairchild® Fairchild Semiconductor® FACT Quiet Series™ FACT FAST® FastvCore™ FETBench™

Green FPS™ Green FPS™ e-Series™ Gmax™ GTO™ IntelliMAX™ ISOPLANAR™ MegaBuck™ MIČROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ Motion-SPM™ OptoHiT™ **OPTOLOGIC[®] OPTOPLANAR[®]** PDP SPM™ Power-SPM™

Global Power Resource SM

PowerTrench[®] PowerXS™ Programmable Active Droop™ QFE1 QS™ Quiet Series™ RapidConfigure™ Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ SPM® STEALTH™ SuperFET™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS™ SyncFET™ Sync-Lock™ SYSTEM[®] GENERAL

TinyBoost™ TinyBoost™ TinyCalc™ TinyCalc™ TinyCojc® TINYOPTO™ TinyPower™ TinyPWM™ TinyPWM™ TriFault Detect™ TRUECURRENT™* µSerDes™



Ultra FRFET™ UniFET™ VCX™ VisualMax™ XS™

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FlashWriter®*

FPS™

F-PFS™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are
 intended for surgical implant into the body or (b) support or sustain life,
 and (c) whose failure to perform when properly used in accordance
 with instructions for use provided in the labeling, can be reasonably
 expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition	of Tormo	

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
		Rev. 147

www.fairchildsemi.com

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

BS170_L34Z MMBF170_D87Z MMBF170_Q BS170_Q